

Principles of Electronics (EC-1304)
END semester examination – 2014
(BTech 3rd semester, EE)

Time: 3:00 Hrs.

Max Marks: 60

Note: Do any TEN questions. All questions carry equal marks.

- Q.1 Perform the following mathematical operations:-
- $(44)_{10} + (24)_{10} = ()_{10}$ using 9's complement.
 - $(19)_{10} - (49)_{10} = ()_2$ using 1's complement.
 - (i) convert $(100110111)_2$ in Gray Code number and (ii) convert Gray code number 1001001101 in Binary number system.
- Q.2 Find the min-term expansion of $f(A, B, C, D) = \bar{A}(\bar{B} + D) + AC\bar{D}$
(Hint: In the range of 0-15).
- Q.3 For the given Boolean expression $f(A, B, C, D) = (\bar{A} + B) \cdot \bar{C} \cdot (1 + D + 0 \cdot \bar{E})$.
Find (a) Dual Function (f_D) and (b) Complement Function (\bar{f}).
- Q.4 The differential input operational amplifier shown in Figure Q.4 consists of a base amplifier of infinite gain. Terminals 1 and 2 are inverting and non-inverting, respectively. Find the output voltage expression.
- Q.5 Draw and explain the (a) OPAMP Logarithmic amplifier and (b) OPAMP Multiplier circuit (for two input signals only).
- Q.6 Draw and explain the hybrid parameter model of a BJT transistor with suitable diagrams. Also, draw and explain the simplified h -parameter model. (Detailed derivations are NOT necessary).
- Q.7 For the self bias FET circuit shown in the Figure Q.7 below, Determine I_{DQ} , V_{GSQ} , and V_{DSQ} . (Given $I_{DSS} = 10 \text{ mA}$ and $V_P = -4 \text{ V}$).
- Q.8 Derive an expression for the r_{ON} (ON state resistance) of a FET for small drain-to-source voltage. (Consider the common notations used in the class for representing different parameters).
- Q.9 Determine the range of R_L and I_L that will result in V_{R_L} being maintained at 10 V consider the circuit shown in Figure Q.9.
- Q.10 Write short notes on (around 100 words for each, DO ANY FOUR)
- Enhancement-type MOSFET
 - Cathode ray oscilloscope (CRO)
 - Function generator
 - Base width modulation or Early effect
 - Diode: Transition capacitance (C_T), and Diffusion capacitance (C_D)
 - Ideal Operational Amplifier (OPAMP)

1. Derive the expression for the ripple factor of a bridge-type full wave rectifier. Find the peak inverse voltage (PIV) across each of the diodes in the above full wave rectifier.

Q.12 Design a clamper to perform the function shown in the Figure Q.12 shown below

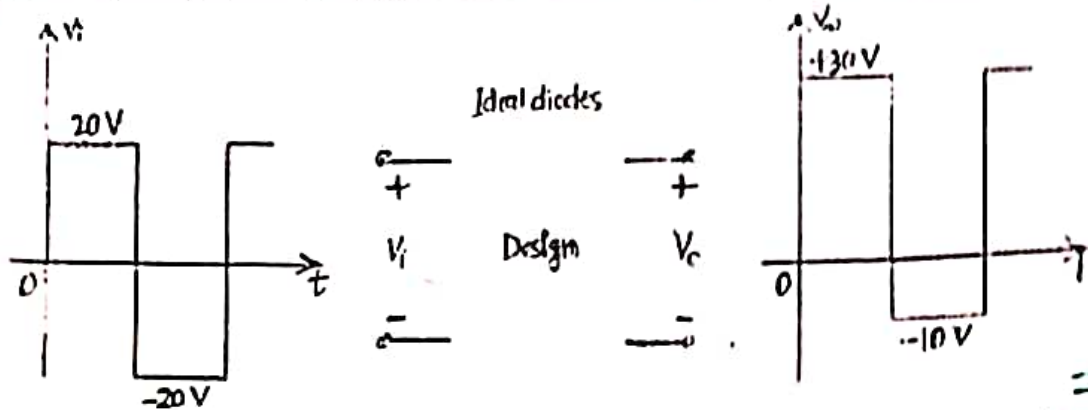


Figure Q.12

Q.13 Determine the DC bias voltage V_{CE} and the current I_C for the voltage divider BJT circuit shown below in Figure Q.13. Given: $\beta = 140$

Problem Figures

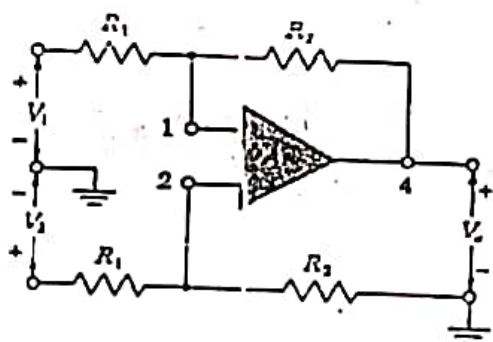


Figure Q.4

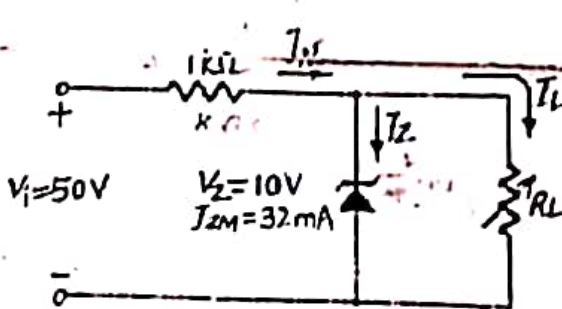


Figure Q.9

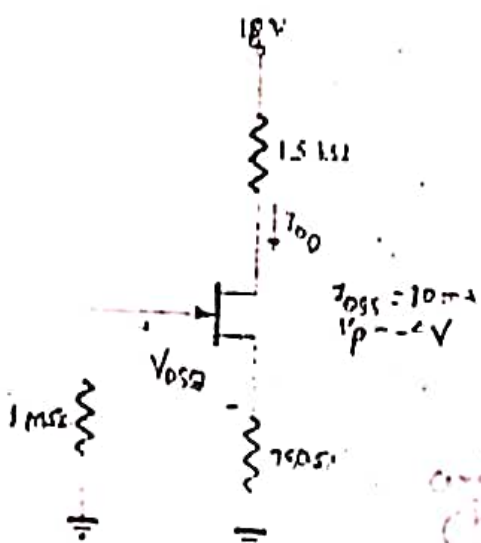


Figure Q.7

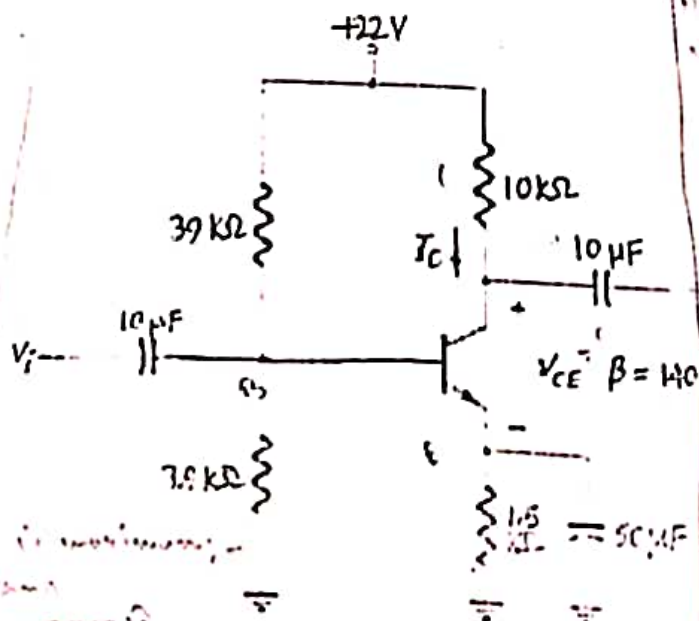


Figure Q.13